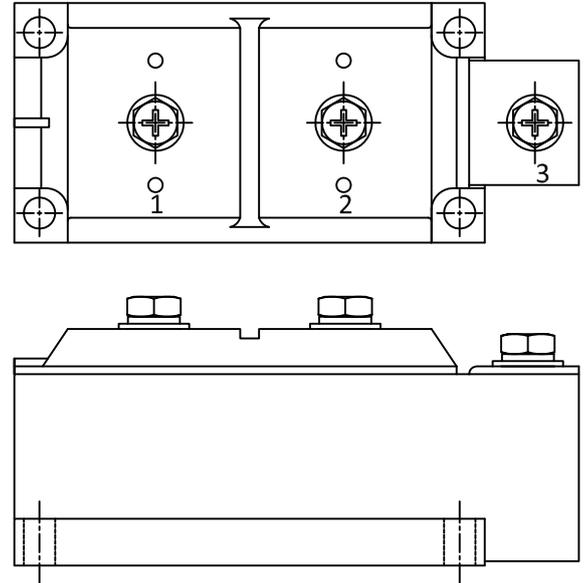


IRK. 500 Series

High Voltage Thyristor/ Diode and Thyristor/ Thyristor

FEATURES

- # Electrically isolated base plate.
- # 3500Vrms isolating voltage.
- # Industrial standard package.
- # Simplified mechanical designs, rapid assembly.
- # High surge capability.
- # Large creepage distance.



DESCRIPTION

These IRK series of Power Modules use power diodes and thyristor in four basic configuration. The semiconductors are electrically isolated from the metal base, allowing common heat sinks and compact assemblies to be built. They can be interconnected to form single phase or three phase bridges or AC switches. when modules are connected in anti-parallel

These module are intended for general purpose applications such as battery chargers.welders and plating equipment.

MAJOR RATING & CHARACTERISTICS

Parameters	IRK. 500	Units
$I_{T(AV)}$ @Tc-85°C	500	A
$I_{T(RMS)}$ @Tc-85°C	785	A
I_{TSM} @ 50Hz	18.0	kA
I^2t @ 50Hz	1620	kA ² s
V_{RRM}	3000 to 3600	V
T_j	-40 to 125	°C

POWER MODULES

IRK. 500 Series

ELECTRICAL SPECIFICATION VOLTAGE RATINGS

Type Number	Voltage Code	V_{RRM} max. repetitive peak reverse and off-state blocking voltage V	V_{RSM} max.non-repetitive peak reverse voltage V	I_{DRM} / I_{RRM} max. @ 125°C Max. mA
IRK.500	30	3000	3100	250
	32	3200	3300	
	34	3400	3500	
	36	3600	3700	

ON-STATE CONDUCTION

	Parameter	IRK.500	Unit	Conditions	
$I_{T(AV)}$	Max, average On-state current @ case temperature	500 85	A °C	180°C conduction, half sine wave	
$I_{T(RMS)}$	Max, RMS on-state current	785	A	as AC switch	
I_{TSM}	Max, peak, one cycle on-state, non-repetitive surge current	18.0	kA	t = 10ms	Sinusoidal half wave initial $T_j = T_j$ max.
I^2t	Maximum I^2t for fusing	1620	kA ² s	t = 10ms	
$V_{T(TO)}$	Max, value of Threshold voltage	1.10	V	$T_j = T_j$ max.	
r_t	Max, value of on-state slope resistance	0.4	mΩ	$T_j = T_j$ max,	
V_{TM}	Max, on-state voltage drop	1.85	V	$I_r = 1570A, 25°C$	
I_H	Maximum holding current	300	mA	$V_D = 12V$, Gate Open $T_j = 25°C$	
I_L	Max, latching current	1500	mA	$T_j = 25°C, V_D = 12V$, Gate pulse $I_G = 2A$ $t_{GP} = 50\mu s$	

SWITCHING

t_d	Typical delay time	3.0	μs	$T_j = 25°C$ Gate current = 1A $di/dt = 1A/\mu s$ $V_d = 0.4\% V_{DRM}$ $I_{TM} = I_{T(AV)}$ $V_G = 20V$ $t_{GP} = 500\mu s$, $di/dt = 1A/\mu s$.
t_q	Typical turn-off time	400	μs	$I_{TM} = I_{T(AV)}$ $di/dt = 10A/\mu s$, $T_j = T_j$ max, $V_r = 100V$, $dv/dt = 50 V/\mu s$. $V_D = 0.67V_{DRM}$

POWER MODULES

IRK. 551 Series

BLOCKING

	Parameter	IRK. 500	Unit	Conditions
dv/dt	Max, critical rate of rise of off-state voltage	1000	V/ μ s	Tj = Tj Max, V _D = 0.67V _{DRM} , Gate Open
I _{RRM} I _{DRM}	Max. peak reverse and off state leakage current at V _{RRM} V _{DRM}	250	mA	Tj = 125°C, rated V _{DRM} /V _{RRM} Applied
V _{INS}	RMS Isolation voltage	3.0	kV	Sine wave, 50Hz, RMS t = 1 min t = 1 sec
		3.6		

ELECTRICAL SPECIFICATION TRIGGERING

	Parameter	IRK. 500	Unit	Conditions
P _{FGM}	Peak forward gate current	8	A	Tj = Tj max,
V _{RGM}	Peak reverse gate voltage	5	V	Tj = Tj max,
P _G	Gate Power dissipation	4	W	Tj = Tj Max, for DC gate current
I _{GT}	DC gate current required to trigger	250	mA	Tj = 25°C V _D = 12V, I _D = 3A
V _{GT}	DC gate voltage required to trigger	2.5	V	
V _{GD}	DC gate voltage not to trigger	0.35	V	Tj = Tj max. V _D = 0.67V _{DRM}
I _{GD}	DC gate current not to trigger	15	mA	
di/dt	Max, critical rate of rise of turned-on current	400	A/ μ s	V _D = 0.67V _{DRM} I _{TM} =2I _{T(AV)}

THERMAL AND MECHANICAL SPECIFICATION

	Parameter	IRK. 500	Unit	Conditions
T _J	Junction operating temperature	-40 to 125	°C	
T _{stg}	Max, storage temperature range	-40 to 125		
R _{thJ-C}	Max. thermal resistance, junction to case Per Module Per arm	0.0250	°C/W	180° half wave 50Hz
		0.0500		
R _{thC-h}	Max. thermal resistance junction to heatsink Per Module Per arm	0.0080	°C/W	
		0.0160		
T	Mounting torque \pm 10%	9 (18)	Nm	For module to heat sink and bus bar to module
Wt	Approximate Weight	3500	g	

